

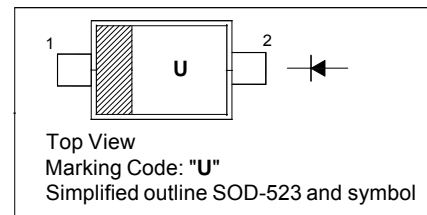
## SILICON BAND SWITCHING DIODE

### Applications

for band switching in VHF television tuners  
and surface mount band switching circuits

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Current	$I_F$	100	mA
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Operating Temperature Range	$T_{op}$	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

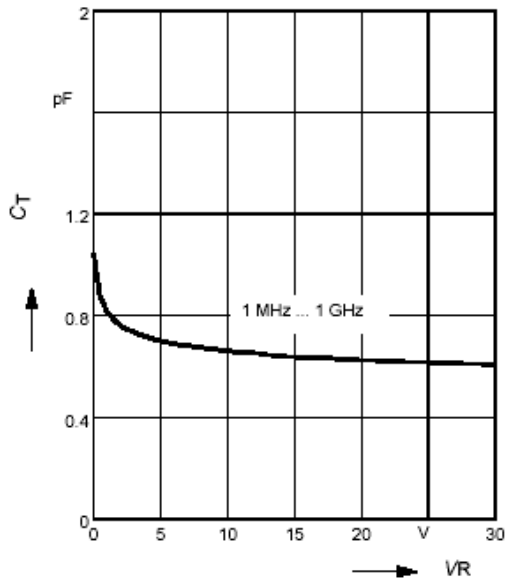
### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Current at $V_R = 20\text{ V}$	$I_R$	-	-	20	nA
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	-	-	1	V
Diode Capacitance at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$ at $V_R = 3\text{ V}$ , $f = 1\text{ MHz}$ at $V_R = 0\text{ V}$ , $f = 100\text{ MHz}$	$C_T$	0.65 0.6 -	- - 1	1.4 1.1 -	pF
Forward Resistance at $I_F = 3\text{ mA}$ , $f = 100\text{ MHz}$ at $I_F = 10\text{ mA}$ , $f = 100\text{ MHz}$	$r_f$	- -	- -	0.7 0.5	$\Omega$
Series Inductance	$L_s$	-	0.6	-	nH

## BA892WT

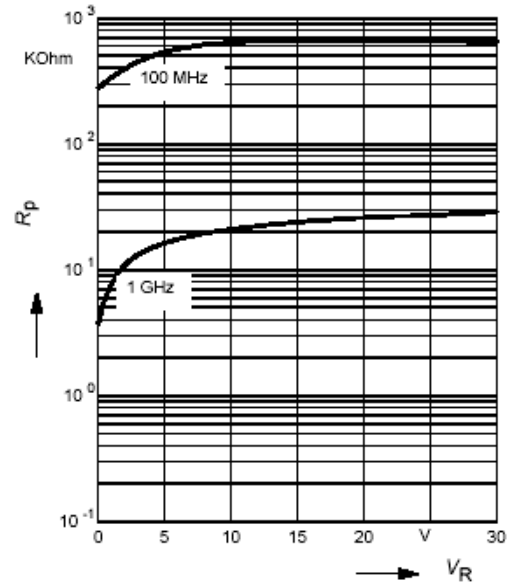
Diode capacitance  $C_T = f(V_R)$

$f =$  Parameter



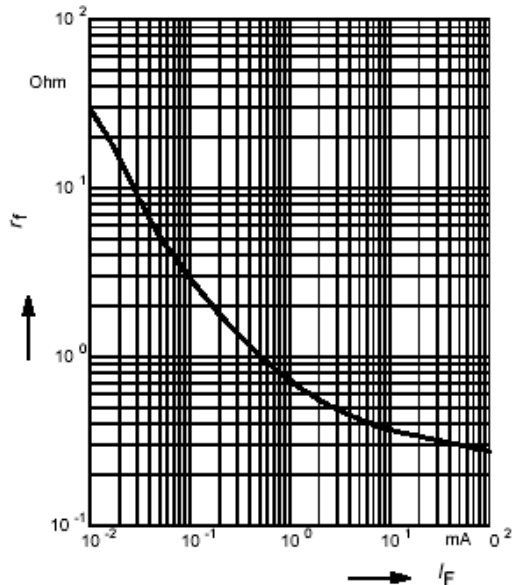
Reverse parallel resistance  $R_P = f(V_R)$

$f =$  Parameter



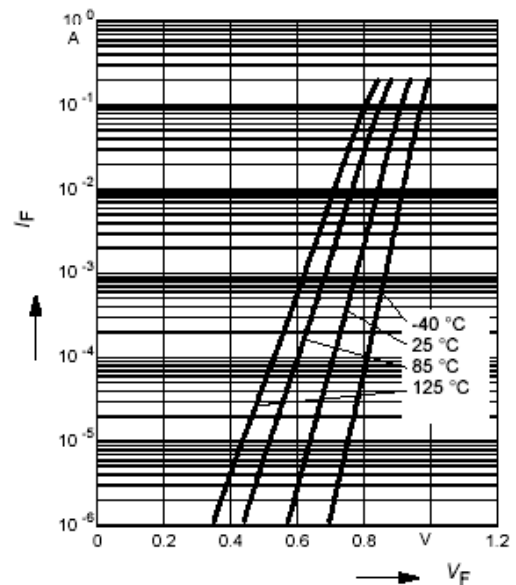
Forward resistance  $r_f = f(I_F)$

$f = 100\text{MHz}$



Forward current  $I_F = f(V_F)$

$T_A =$  Parameter





**CHINA BASE**  
INTERNATIONAL

**SOD-523**

**BA892WT**



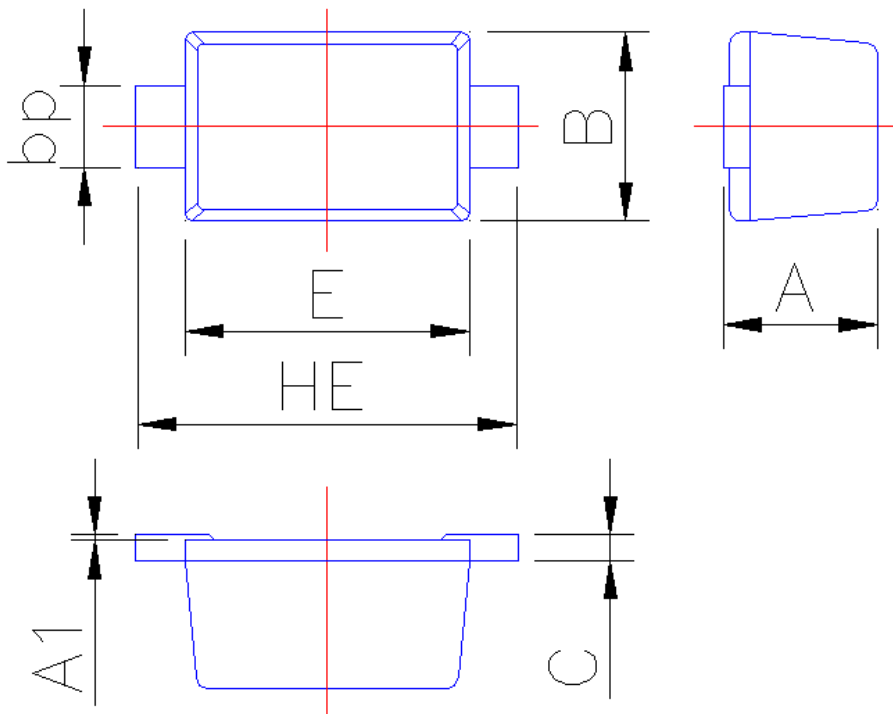
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**BA892WT**

**PACKAGE OUTLINE**

SOD-523

Plastic surface mounted package; 2 leads



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70